Unit in mm

TOSHIBA Photocoupler GaAlAs Ired & Photo-Triac

TLP668J

Office Machine.

Household Use Equipment.

Triac Driver.

Solid State Relay.

The TOSHIBA TLP668J consists of a zero voltage crossing turn—on photo—triac optically coupled to a GaA ℓ As infrared emitting diode in a six lead plastic DIP package.

- Peak off-state voltage: 600V (min.)
- Trigger LED current: 3mA (max.)
- On-state current: 100mA(max.)
- Isolation voltage: 5000Vrms (min.)
- UL recognized: UL1577, file No.E67349

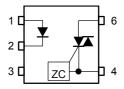
3 2 1 0 7.62 8.64±0.25 8.64±0.25 1.2 0.5 1.85~8.80

Weight: 0.44g

JEDEC EIAJ TOSHIBA

Pin Configuration (top view)

11-9A2



- 1 : Anode
- 2 : Cathode
- 3 : NC
- 4 : Terminal 1
- 6: Terminal 2

(Z, C, : Zero-cross Circuit)

Maximum Ratings (Ta = 25°C)

	Characteristic Forward current		Symbol	Rating	Unit	
	Forward current		l _F	30	mA	
	Forward current derating (Ta = 25°C)		ΔI _F / °C	-0.3	mA / °C	
TED	Peak forward current (100µs pulse, 100pps)		I _{FP}	1	Α	
	Reverse voltage		V _R	5	V	
	Junction temperature		Tj	125	°C	
	Off-state output terminal voltage	V_{DRM}	600	V		
	On-state RMS current	Ta = 25°C	l=(DMO)	100	mA	
ō		Ta = 70°C	I _{T(RMS)}	50	ША	
Detector	On–state current derating (Ta = 25°C)		ΔI _T / °C	-1.1	mA / °C	
ă	Peak on-state current (100µs pulse, 120pps)		I _{TP}	2	Α	
	Peak nonrepetitive surge current (P _W = 10ms, DC = 10%)		I _{TSM}	1.2	Α	
	Junction temperature	Tj	110	°C		
Storage	e temperature range		T _{stg}	−55~150	°C	
Operat	Operating temperature range			−40~100	°C	
Lead s	Lead soldering temperature (10sec.)			260	°C	
Isolatio	on voltage (AC, 1min., R.H. 60%)	BV_S	5000	Vrms		

(Note 1): Device considered a two terminal device: Pins1,2 and 3 shorted together and pins 4 and 6 shorted together.

Individual Electrical Characteristics (Ta = 25°C)

	Characteristic	Symbol	Test Condition	Min.	Тур.	Max.	Unit
LED	Forward voltage	V _F	I _F = 10mA	1.2	1.4	1.7	V
	Reverse current	I _R	V _R = 3 V	_	_	10	μΑ
	Capacitance	C _T	V = 0, f = 1MHz	_	30	_	pF
Detector	Peak off-state current	I _{DRM}	V _{DRM} = 600V	_	10	1000	nA
	Peak on-state voltage	V _{TM}	I _{TM} = 100mA	_	_	3.0	V
	Holding current	lн	_	_	0.2	_	mA
	Critical rate of rise of off–state voltage	dv / dt	V _{in} = 240rms Ta = 85°C	_	500	_	V/µs
	Critical rate of rise of commutating voltage	dv / dt(c)	V _{in} = 60Vrms I _T = 15mArms		0.2	_	V/µs

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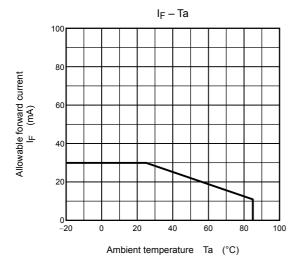
Coupled Electrical Characteristics (Ta = 25°C)

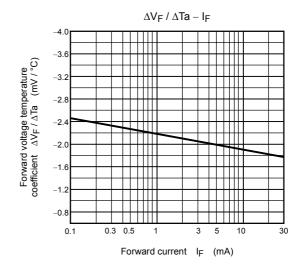
Characteristics	Symbol	Test Condition	Min.	Тур.	Max.	Unit
Trigger LED current	I _{FT}	V _T = 6V, resistive load	_	_	3	mA
Inhibit voltage	V _{IH}	I _F = rated I _{FT}	_	_	50	V
Leakage in inhibited state	lін	I _F = rated I _{FT} V _T = rated V _{DRM}	_	_	600	μΑ
Capacitance input to output	CS	V _S = 0, f = 1MHz	_	0.8	_	pF
Isolation resistance	R _S	V _S = 500V, R.H. ≤ 60%	5×10 ¹⁰	10 ¹⁴	_	Ω
	BVS	AC, 1 minute	5000	_	_	V
Isolation voltage		AC, 1 second(in oil)	_	10000	_	V _{rms}
		DC, 1 minute(in oil)	_	10000	_	Vdc

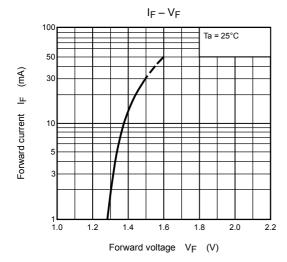
Recommended Operating Conditions

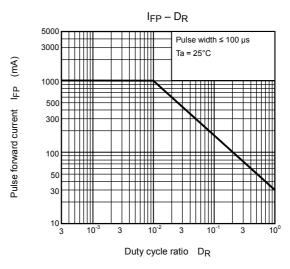
Characteristic	Symbol	Min.	Тур.	Max.	Unit
Supply voltage	V _{AC}	_	_	240	Vac
Forward current	lF	4.5	6	7.5	mA
Peak on-state current	I _{TP}	_	_	1	Α
Operating temperature	T _{opr}	-10	_	85	°C

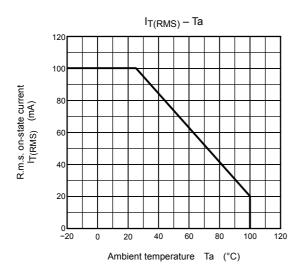
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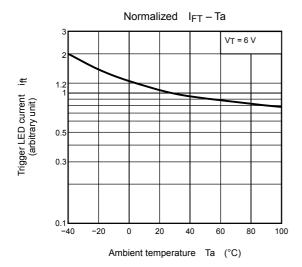


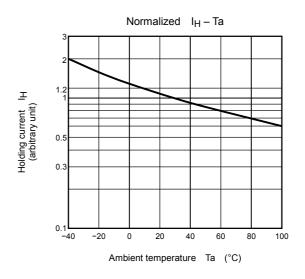


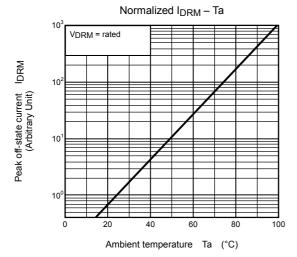


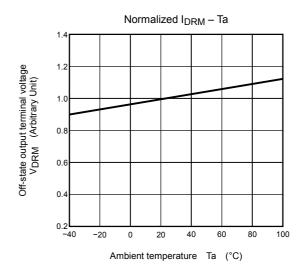


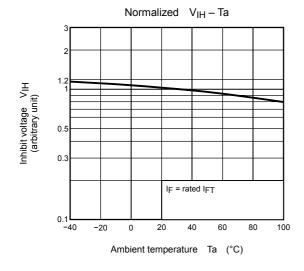


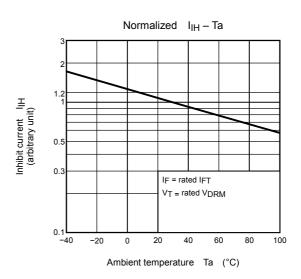












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